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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LCD, LVD, POR, PWM, WDT
Number of I/O	59
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 35x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mk51dn512zcll10

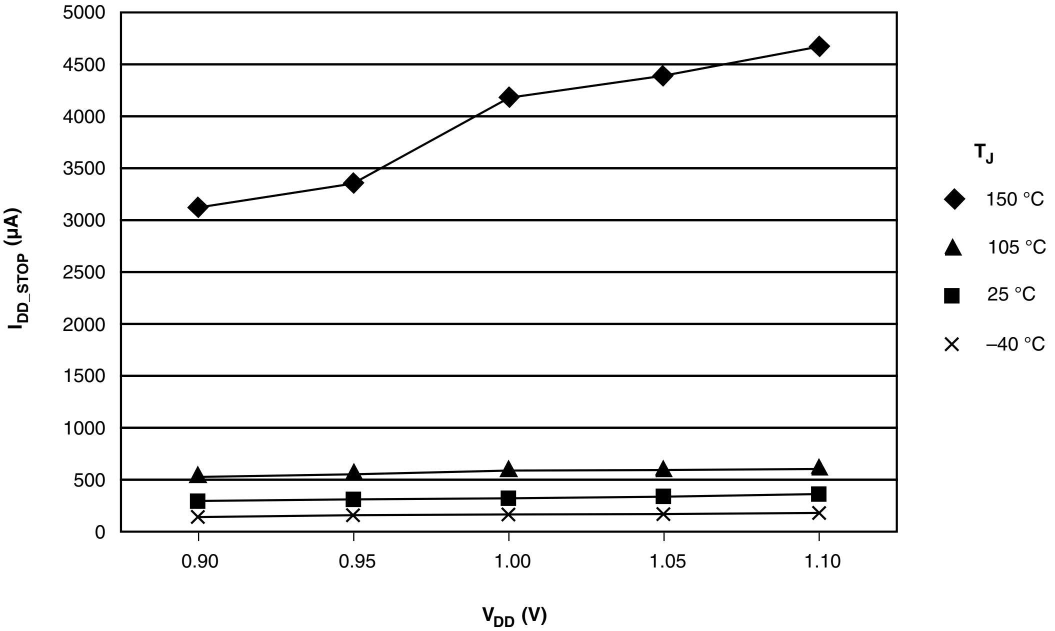
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	185	mA
V_{DIO}	Digital input voltage (except $\overline{RESET}$, EXTAL, and XTAL)	–0.3	5.5	V
V_{AIO}	Analog[1], $\overline{RESET}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Maximum current single pin limit (applies to all digital pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{USB_DP}	USB_DP input voltage	–0.3	3.63	V
V_{USB_DM}	USB_DM input voltage	–0.3	3.63	V
VREGIN	USB regulator input	–0.3	6.0	V
V_{BAT}	RTC battery supply voltage	–0.3	3.8	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

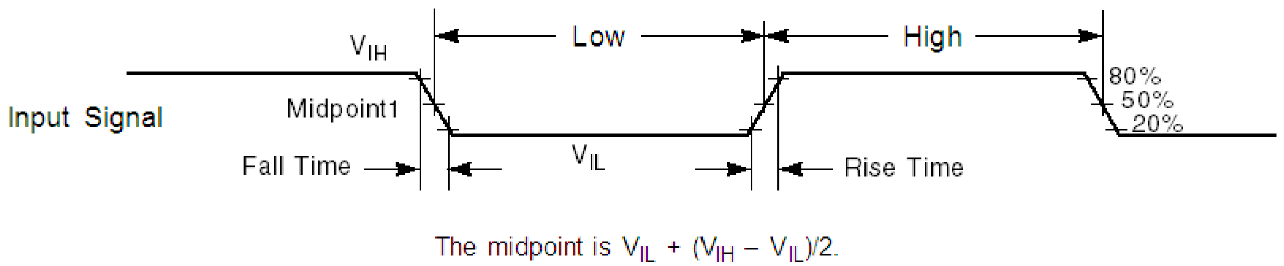


Figure 1. Input signal measurement reference

All digital I/O switching characteristics assume:

1. output pins
   - have C_L=30pF loads,
   - are configured for fast slew rate (PORTx_PCRn[SRE]=0), and
   - are configured for high drive strength (PORTx_PCRn[DSE]=1)
2. input pins
   - have their passive filter disabled (PORTx_PCRn[PFE]=0)

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 0.7 × V_{DD} 0.75 × V_{DD}	 — —	 V V	
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 — —	 0.35 × V_{DD} 0.3 × V_{DD}	 V V	
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	
I_{ICDIO}	Digital pin negative DC injection current — single pin • V_{IN} < V_{SS}-0.3V	-5	—	mA	1
I_{ICAIO}	Analog[2], EXTAL, and XTAL pin DC injection current — single pin • V_{IN} < V_{SS}-0.3V (Negative current injection) • V_{IN} > V_{DD}+0.3V (Positive current injection)	 -5 —	 — +5	mA	3
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 -25 —	 — +25	mA	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	4
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All 5 V tolerant digital I/O pins are internally clamped to V_{SS} through an ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} is less than V_{DIO_MIN}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO\_MIN}-V_{IN})/|I_{ICDIO}|$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function. Additionally, EXTAL and XTAL are analog pins.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{ICAIO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO\_MAX})/|I_{ICAIO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.
4. Open drain outputs must be pulled to VDD.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength					
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -9mA	V_{DD} – 0.5	—	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -3mA	V_{DD} – 0.5	—	—	V	
	Output high voltage — low drive strength					
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2mA	V_{DD} – 0.5	—	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -0.6mA	V_{DD} – 0.5	—	—	V	
I_{OHT}	Output high current total for all ports	—	—	100	mA	
V_{OL}	Output low voltage — high drive strength					2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 9mA	—	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 3mA	—	—	0.5	V	
	Output low voltage — low drive strength					
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 2mA	—	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 0.6mA	—	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	—	100	mA	
I_{INA}	Input leakage current, analog pins and digital pins configured as analog inputs					3, 4
	• V_{SS} ≤ V_{IN} ≤ V_{DD}					
	• All pins except EXTAL32, XTAL32, EXTAL, XTAL	—	0.002	0.5	μA	
	• EXTAL (PTA18) and XTAL (PTA19)	—	0.004	1.5	μA	
	• EXTAL32, XTAL32	—	0.075	10	μA	
I_{IND}	Input leakage current, digital pins					4, 5
	• V_{SS} ≤ V_{IN} ≤ V_{IL}					
	• All digital pins	—	0.002	0.5	μA	
	• V_{IN} = V_{DD}					
	• All digital pins except PTD7	—	0.002	0.5	μA	
	• PTD7	—	0.004	1	μA	
I_{IND}	Input leakage current, digital pins					4, 5, 6
	• V_{IL} < V_{IN} < V_{DD}					
	• V_{DD} = 3.6 V	—	18	26	μA	
	• V_{DD} = 3.0 V	—	12	49	μA	
	• V_{DD} = 2.5 V	—	8	13	μA	
	• V_{DD} = 1.7 V	—	3	6	μA	

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	N/A	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	—	N/A	—	mA	8
I_{DD_STOP}	Stop mode current at 3.0 V					
	• @ –40 to 25°C	—	0.59	1.4	mA	
	• @ 70°C	—	2.26	7.9	mA	
	• @ 105°C	—	5.94	19.2	mA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	• @ –40 to 25°C	—	93	435	μA	
	• @ 70°C	—	520	2000	μA	
	• @ 105°C	—	1350	4000	μA	
I_{DD_LLS}	Low leakage stop mode current at 3.0 V					9
	• @ –40 to 25°C	—	4.8	20	μA	
	• @ 70°C	—	28	68	μA	
	• @ 105°C	—	126	270	μA	
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					9
	• @ –40 to 25°C	—	3.1	8.9	μA	
	• @ 70°C	—	17	35	μA	
	• @ 105°C	—	82	148	μA	
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					
	• @ –40 to 25°C	—	2.2	5.4	μA	
	• @ 70°C	—	7.1	12.5	μA	
	• @ 105°C	—	41	125	μA	
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	• @ –40 to 25°C	—	2.1	7.6	μA	
	• @ 70°C	—	6.2	13.5	μA	
	• @ 105°C	—	30	46	μA	
I_{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V					
	• @ –40 to 25°C	—	0.33	0.39	μA	
	• @ 70°C	—	0.60	0.78	μA	
	• @ 105°C	—	1.97	2.9	μA	

Table continues on the next page...

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 Debug trace timing specifications

Table 12. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
T_{cyc}	Clock period	Frequency dependent		MHz
T_{wl}	Low pulse width	2	—	ns
T_{wh}	High pulse width	2	—	ns
T_r	Clock and data rise time	—	3	ns
T_f	Clock and data fall time	—	3	ns
T_s	Data setup	3	—	ns
T_h	Data hold	2	—	ns

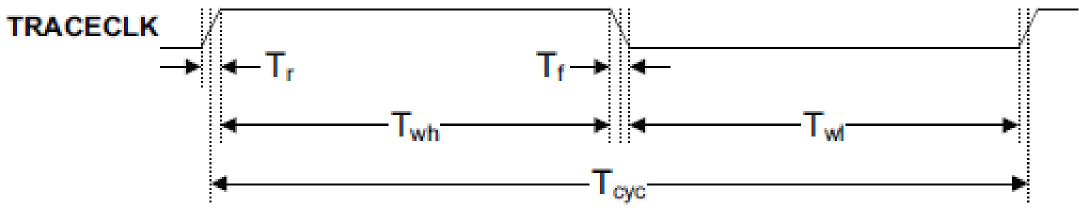


Figure 3. TRACE_CLKOUT specifications

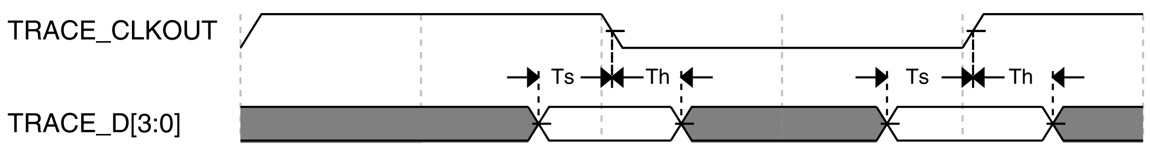


Figure 4. Trace data specifications

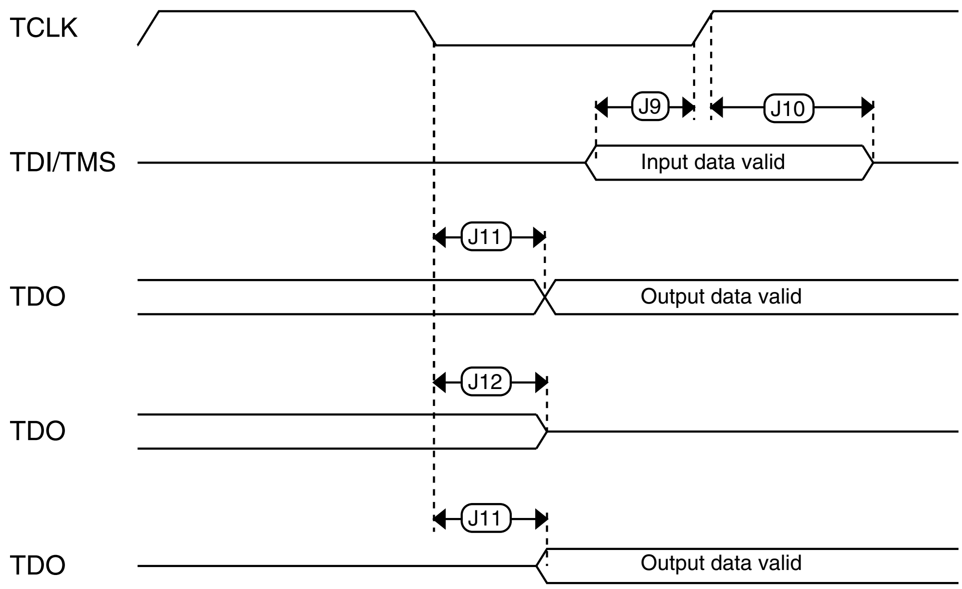


Figure 7. Test Access Port timing

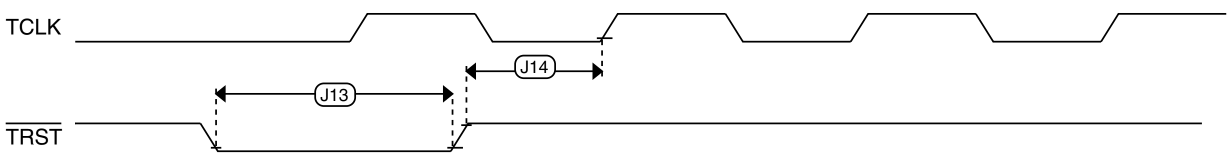


Figure 8. $\overline{\text{TRST}}$ timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

6.4.1.5 Write endurance to FlexRAM for EEPROM

When the FlexNVM partition code is not set to full data flash, the EEPROM data set size can be set to any of several non-zero values.

The bytes not assigned to data flash via the FlexNVM partition code are used by the flash memory module to obtain an effective endurance increase for the EEPROM data. The built-in EEPROM record management system raises the number of program/erase cycles that can be attained prior to device wear-out by cycling the EEPROM data through a larger EEPROM NVM storage space.

While different partitions of the FlexNVM are available, the intention is that a single choice for the FlexNVM partition code and EEPROM data set size is used throughout the entire lifetime of a given application. The EEPROM endurance equation and graph shown below assume that only one configuration is ever used.

$$\text{Writes\_subsystem} = \frac{\text{EEPROM} - 2 \times \text{EEESPLIT} \times \text{EEESIZE}}{\text{EEESPLIT} \times \text{EEESIZE}} \times \text{Write\_efficiency} \times n_{nvmcycd}$$

where

- Writes_subsystem — minimum number of writes to each FlexRAM location for subsystem (each subsystem can have different endurance)
- EEPROM — allocated FlexNVM for each EEPROM subsystem based on DEPART; entered with the Program Partition command
- EEESPLIT — FlexRAM split factor for subsystem; entered with the Program Partition command
- EEESIZE — allocated FlexRAM based on DEPART; entered with the Program Partition command
- Write_efficiency —
  - 0.25 for 8-bit writes to FlexRAM
  - 0.50 for 16-bit or 32-bit writes to FlexRAM
- $n_{nvmcycd}$ — data flash cycling endurance (the following graph assumes 10,000 cycles)

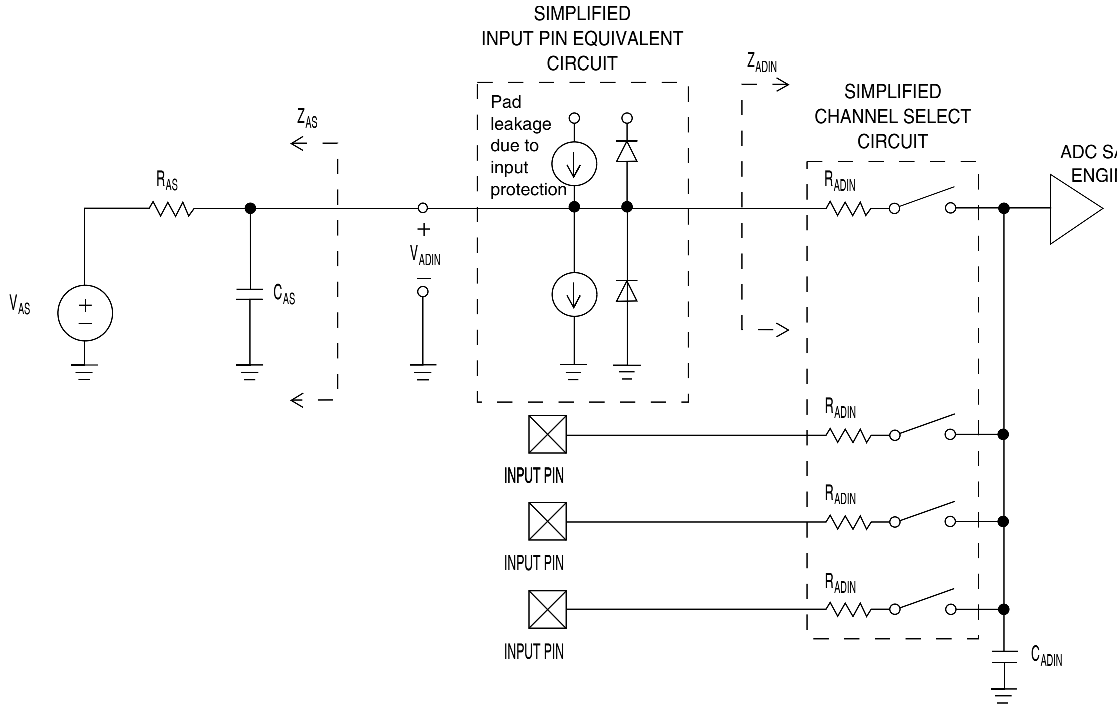


Figure 11. ADC input impedance equivalency diagram

6.6.1.2 16-bit ADC electrical characteristics

Table 26. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	-4 -1.4	-5.4 -1.8	LSB[4]	$V_{ADIN} = V_{DDA}$ 5

Table continues on the next page...

Table 26. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
E_Q	Quantization error	• 16-bit modes • ≤13-bit modes	— —	-1 to 0 —	— ±0.5	LSB[4]	
ENOB	Effective number of bits	16-bit differential mode • Avg = 32 • Avg = 4 16-bit single-ended mode • Avg = 32 • Avg = 4	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 × ENOB + 1.76			dB	
THD	Total harmonic distortion	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	— —	–94 -85	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	82 78	95 90	— —	dB dB	7
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.

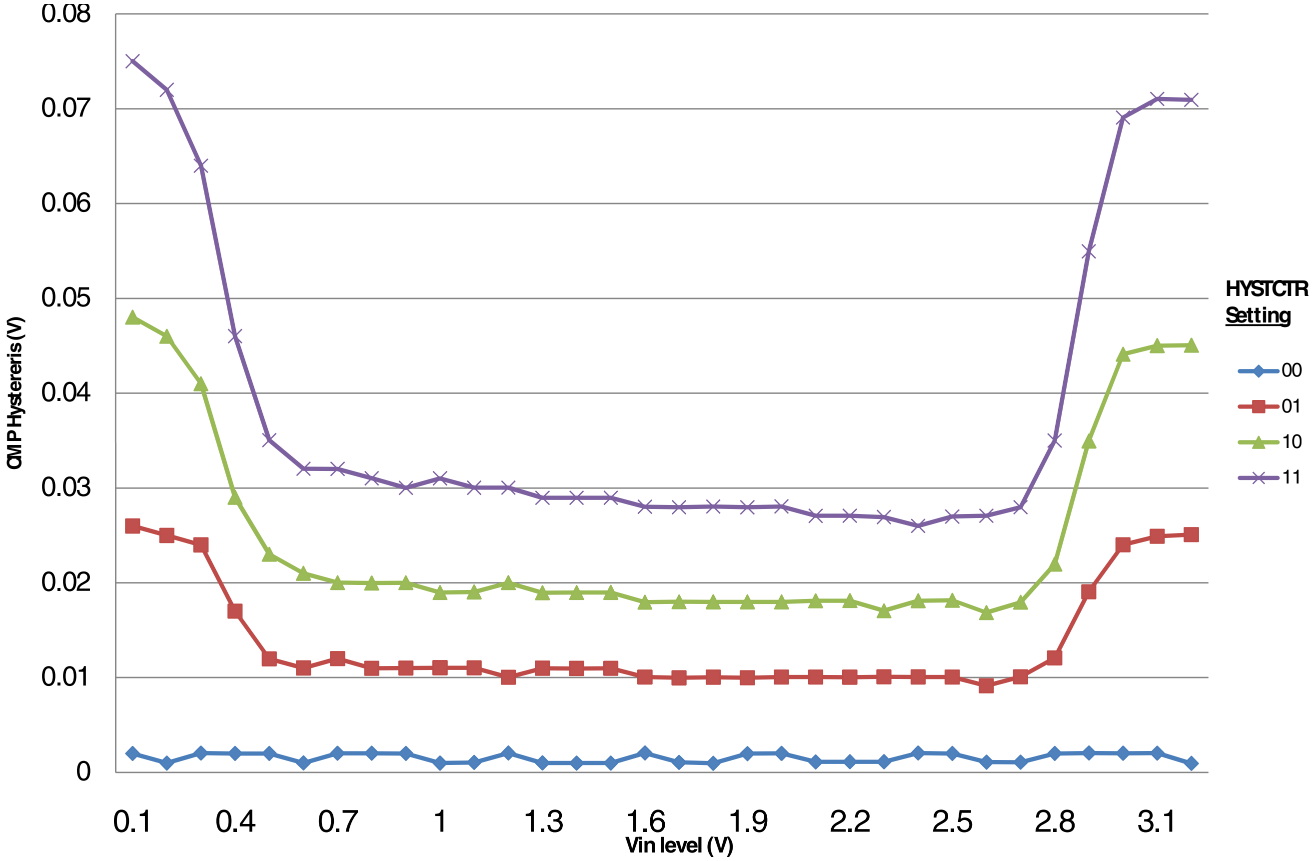


Figure 14. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=0)

6.6.3.2 12-bit DAC operating behaviors

Table 31. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	150	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	700	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4$ V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance load = 3 kΩ	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

Table 34. TRIAMP full range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{SUPPLY}	Supply current (I_{OUT}=0mA, CL=0) — Low-power mode	—	60	80	μA	
I_{SUPPLY}	Supply current (I_{OUT}=0mA, CL=0) — High-speed mode	—	280	450	μA	
V_{OS}	Input offset voltage	—	±3	±5	mV	
α_{VOS}	Input offset voltage temperature coefficient	—	4.8	—	μV/C	
I_{OS}	Input offset current	—	±0.3	±5	nA	
I_{BIAS}	Input bias current	—	±0.3	±5	nA	
R_{IN}	Input resistance	500	—	—	MΩ	
C_{IN}	Input capacitance	—	17	—	pF	
R_{OUT}	Output AC impedance	—	—	1500	Ω	@ 100kHz, High speed mode
$\lvert X_{IN}\rvert$	AC input impedance (f_{IN}=100kHz)	—	159	—	kΩ	
CMRR	Input common mode rejection ratio	60	—	—	dB	
PSRR	Power supply rejection ratio	60	—	—	dB	
SR	Slew rate (ΔV_{IN}=100mV) — Low-power mode	0.1	—	—	V/μs	
SR	Slew rate (ΔV_{IN}=100mV) — High speed mode	1	—	—	V/μs	
GBW	Unity gain bandwidth — Low-power mode 50pF	0.15	—	—	MHz	
GBW	Unity gain bandwidth — High speed mode 50pF	1	—	—	MHz	
A_V	DC open-loop voltage gain	80	—	—	dB	
VOUT	Output voltage range	0.15	—	V_{DD}-0.15	V	
I_{OUT}	Output load current	—	±0.5	—	mA	
GM	Gain margin	—	20	—	dB	
PM	Phase margin	50	60	—	deg	
Vn	Voltage noise density (noise floor) 1kHz	—	280	—	nV/√Hz	
Vn	Voltage noise density (noise floor) 10kHz	—	100	—	nV/√Hz	

6.6.6 Transimpedance amplifier electrical specifications — limited range

Table 35. TRIAMP limited range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	2.4	3.3	V	
V_{IN}	Input voltage range	0.1	V_{DDA}-1.4	V	
T_A	Temperature	0	50	C	
C_L	Output load capacitance	—	100	pf	

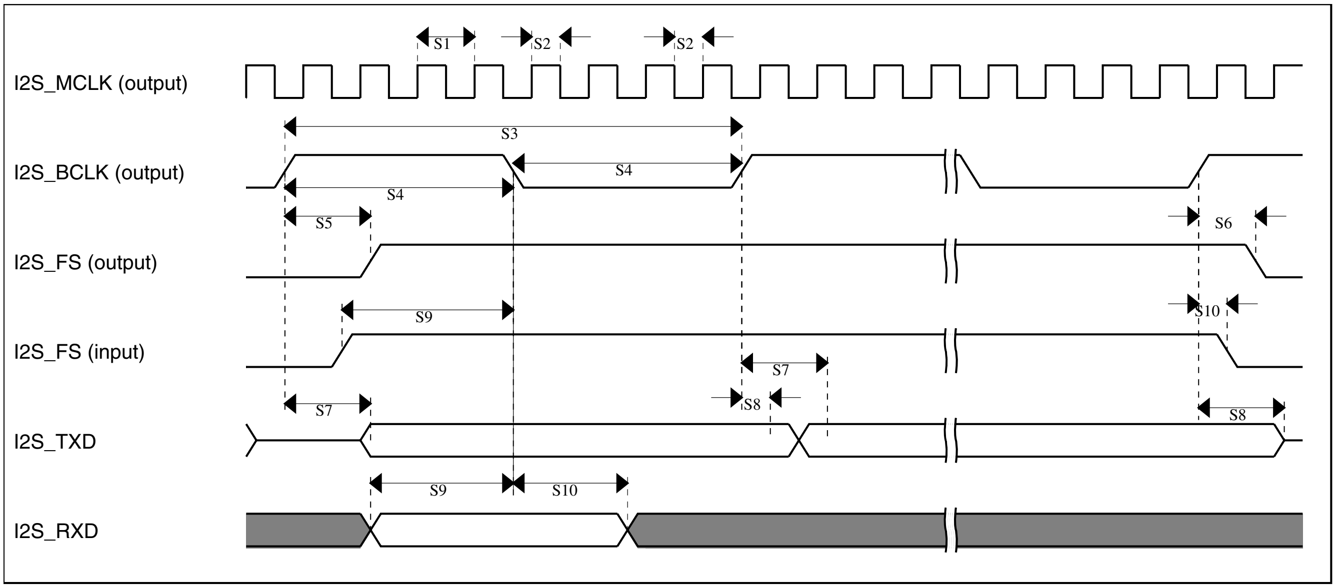


Figure 24. I²S timing — master mode

Table 50. I²S slave mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S11	I2S_BCLK cycle time (input)	8 x t_{SYS}	—	ns
S12	I2S_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_FS input setup before I2S_BCLK	10	—	ns
S14	I2S_FS input hold after I2S_BCLK	3	—	ns
S15	I2S_BCLK to I2S_TXD/I2S_FS output valid	—	20	ns
S16	I2S_BCLK to I2S_TXD/I2S_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_BCLK	2	—	ns

6.9.2 LCD electrical characteristics

Table 54. LCD electricals

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{Frame}	LCD frame frequency	28	30	58	Hz	
C_{LCD}	LCD charge pump capacitance — nominal value	—	100	—	nF	1
C_{BYLCD}	LCD bypass capacitance — nominal value	—	100	—	nF	1
C_{Glass}	LCD glass capacitance	—	2000	8000	pF	2
V_{IREG}	V_{IREG} • HREFSEL=0, RVTRIM=1111 • HREFSEL=0, RVTRIM=1000 • HREFSEL=0, RVTRIM=0000 • HREFSEL=1, RVTRIM=1111 • HREFSEL=1, RVTRIM=1000 • HREFSEL=1, RVTRIM=0000	 — — — — — —	 1.11 1.01 0.91 1.84 1.69 1.54	 — — — — — —	 V V V V V V	3
Δ_{RTRIM}	V_{IREG} TRIM resolution	—	—	3.0	% V_{IREG}	
—	V_{IREG} ripple • HREFSEL = 0 • HREFSEL = 1	 — —	 — —	 30 50	 mV mV	
I_{VIREG}	V_{IREG} current adder — RVEN = 1	—	1	—	µA	4
I_{RBIAS}	RBIAS current adder • LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF) • LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF)	 — —	 10 1	 — —	 µA µA	
R_{RBIAS}	RBIAS resistor values • LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF) • LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF)	 — —	 0.28 2.98	 — —	 MΩ MΩ	
VLL2	VLL2 voltage • HREFSEL = 0 • HREFSEL = 1	 2.0 – 5% 3.3 – 5%	 2.0 3.3	 — —	 V V	
VLL3	VLL3 voltage • HREFSEL = 0 • HREFSEL = 1	 3.0 – 5% 5 – 5%	 3.0 5	 — —	 V V	

1. The actual value used could vary with tolerance.

100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
55	PTB2	LCD_P2/ ADC0_SE12/ TSI0_CH7	LCD_P2/ ADC0_SE12/ TSI0_CH7	PTB2	I2C0_SCL	UART0_RTS_b			FTM0_FLT3	LCD_P2	
56	PTB3	LCD_P3/ ADC0_SE13/ TSI0_CH8	LCD_P3/ ADC0_SE13/ TSI0_CH8	PTB3	I2C0_SDA	UART0_CTS_b			FTM0_FLT0	LCD_P3	
57	PTB7	LCD_P7/ ADC1_SE13	LCD_P7/ ADC1_SE13	PTB7						LCD_P7	
58	PTB8	LCD_P8	LCD_P8	PTB8		UART3_RTS_b				LCD_P8	
59	PTB9	LCD_P9	LCD_P9	PTB9	SPI1_PCS1	UART3_CTS_b				LCD_P9	
60	PTB10	LCD_P10/ ADC1_SE14	LCD_P10/ ADC1_SE14	PTB10	SPI1_PCS0	UART3_RX			FTM0_FLT1	LCD_P10	
61	PTB11	LCD_P11/ ADC1_SE15	LCD_P11/ ADC1_SE15	PTB11	SPI1_SCK	UART3_TX			FTM0_FLT2	LCD_P11	
62	PTB16	LCD_P12/ TSI0_CH9	LCD_P12/ TSI0_CH9	PTB16	SPI1_SOUT	UART0_RX			EWM_IN	LCD_P12	
63	PTB17	LCD_P13/ TSI0_CH10	LCD_P13/ TSI0_CH10	PTB17	SPI1_SIN	UART0_TX			EWM_OUT_b	LCD_P13	
64	PTB18	LCD_P14/ TSI0_CH11	LCD_P14/ TSI0_CH11	PTB18		FTM2_CH0	I2S0_TX_BCLK		FTM2_QD_ PHA	LCD_P14	
65	PTB19	LCD_P15/ TSI0_CH12	LCD_P15/ TSI0_CH12	PTB19		FTM2_CH1	I2S0_TX_FS		FTM2_QD_ PHB	LCD_P15	
66	PTB20	LCD_P16	LCD_P16	PTB20	SPI2_PCS0				CMP0_OUT	LCD_P16	
67	PTB21	LCD_P17	LCD_P17	PTB21	SPI2_SCK				CMP1_OUT	LCD_P17	
68	PTB22	LCD_P18	LCD_P18	PTB22	SPI2_SOUT				CMP2_OUT	LCD_P18	
69	PTB23	LCD_P19	LCD_P19	PTB23	SPI2_SIN	SPI0_PCS5				LCD_P19	
70	PTC0	LCD_P20/ ADC0_SE14/ TSI0_CH13	LCD_P20/ ADC0_SE14/ TSI0_CH13	PTC0	SPI0_PCS4	PDB0_EXTRG	I2S0_TXD			LCD_P20	
71	PTC1/ LLWU_P6	LCD_P21/ ADC0_SE15/ TSI0_CH14	LCD_P21/ ADC0_SE15/ TSI0_CH14	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_b	FTM0_CH0			LCD_P21	
72	PTC2	LCD_P22/ ADC0_SE4b/ CMP1_IN0/ TSI0_CH15	LCD_P22/ ADC0_SE4b/ CMP1_IN0/ TSI0_CH15	PTC2	SPI0_PCS2	UART1_CTS_b	FTM0_CH1			LCD_P22	
73	PTC3/ LLWU_P7	LCD_P23/ CMP1_IN1	LCD_P23/ CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2			LCD_P23	
74	VSS	VSS	VSS								
75	VLL3	VLL3	VLL3								
76	VLL2	VLL2	VLL2								
77	VLL1	VLL1	VLL1								
78	VCAP2	VCAP2	VCAP2								
79	VCAP1	VCAP1	VCAP1								
80	PTC4/ LLWU_P8	LCD_P24	LCD_P24	PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3		CMP1_OUT	LCD_P24	

100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
81	PTC5/ LLWU_P9	LCD_P25	LCD_P25	PTC5/ LLWU_P9	SPI0_SCK		LPT0_ALT2		CMP0_OUT	LCD_P25	
82	PTC6/ LLWU_P10	LCD_P26/ CMP0_IN0	LCD_P26/ CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_EXTRG				LCD_P26	
83	PTC7	LCD_P27/ CMP0_IN1	LCD_P27/ CMP0_IN1	PTC7	SPI0_SIN					LCD_P27	
84	PTC8	LCD_P28/ ADC1_SE4b/ CMP0_IN2	LCD_P28/ ADC1_SE4b/ CMP0_IN2	PTC8		I2S0_MCLK	I2S0_CLKIN			LCD_P28	
85	PTC9	LCD_P29/ ADC1_SE5b/ CMP0_IN3	LCD_P29/ ADC1_SE5b/ CMP0_IN3	PTC9			I2S0_RX_BCLK		FTM2_FLT0	LCD_P29	
86	PTC10	LCD_P30/ ADC1_SE6b/ CMP0_IN4	LCD_P30/ ADC1_SE6b/ CMP0_IN4	PTC10	I2C1_SCL		I2S0_RX_FS			LCD_P30	
87	PTC11/ LLWU_P11	LCD_P31/ ADC1_SE7b	LCD_P31/ ADC1_SE7b	PTC11/ LLWU_P11	I2C1_SDA		I2S0_RXD			LCD_P31	
88	VSS	VSS	VSS								
89	VDD	VDD	VDD								
90	PTC16	LCD_P36	LCD_P36	PTC16		UART3_RX				LCD_P36	
91	PTC17	LCD_P37	LCD_P37	PTC17		UART3_TX				LCD_P37	
92	PTC18	LCD_P38	LCD_P38	PTC18		UART3_RTS_b				LCD_P38	
93	PTD0/ LLWU_P12	LCD_P40	LCD_P40	PTD0/ LLWU_P12	SPI0_PCS0	UART2_RTS_b				LCD_P40	
94	PTD1	LCD_P41/ ADC0_SE5b	LCD_P41/ ADC0_SE5b	PTD1	SPI0_SCK	UART2_CTS_b				LCD_P41	
95	PTD2/ LLWU_P13	LCD_P42	LCD_P42	PTD2/ LLWU_P13	SPI0_SOUT	UART2_RX				LCD_P42	
96	PTD3	LCD_P43	LCD_P43	PTD3	SPI0_SIN	UART2_TX				LCD_P43	
97	PTD4/ LLWU_P14	LCD_P44	LCD_P44	PTD4/ LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4		EWM_IN	LCD_P44	
98	PTD5	LCD_P45/ ADC0_SE6b	LCD_P45/ ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_b	FTM0_CH5		EWM_OUT_b	LCD_P45	
99	PTD6/ LLWU_P15	LCD_P46/ ADC0_SE7b	LCD_P46/ ADC0_SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6		FTM0_FLT0	LCD_P46	
100	PTD7	LCD_P47	LCD_P47	PTD7	CMT_IRO	UART0_TX	FTM0_CH7		FTM0_FLT1	LCD_P47	

8.2 K51 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

Table 55. Revision History (continued)

Rev. No.	Date	Substantial Changes
6	01/2012	• Added AC electrical specifications. • Replaced TBDs with silicon data throughout. • In "Power mode transition operating behaviors" table, removed entry times. • Updated "EMC radiated emissions operating behaviors" to remove SAE level and also added data for 144LQFP. • Clarified "EP7" in "EzPort switching specifications" table and "EzPort Timing Diagram". • Added "ENOB vs. ADC_CLK for 16-bit differential and 16-bit single-ended modes" figures. • Updated I_{DD_RUN} numbers in 'Power consumption operating behaviors' section. • Clarified 'Diagram: Typical IDD_RUN operating behavior' section and updated 'Run mode supply current vs. core frequency — all peripheral clocks disabled' figure. • In 'Voltage reference electrical specifications' section, updated C_L, V_{tdrift}, and V_{vdrift} values. • In 'USB electrical specifications' section, updated V_{DP_SRC}, I_{DDstby}, and '$V_{Reg33out}$ values. • In 'LCD electrical characteristics' section, updated V_{IREG} and Δ_{RTRIM} values.
7	02/2013	• In "ESD handling ratings", added a note for I_{LAT}. • Updated "Voltage and current operating requirements". • Updated "Voltage and current operating behaviors". • Updated "Power mode transition operating behaviors". • Updated "EMC radiated emissions operating behaviors" to add MAPBGA data. • In "MCG specifications", updated the description of f_{ints_t}. • In "16-bit ADC operating conditions", updated the max spec of V_{ADIN}. • In "16-bit ADC electrical characteristics", updated the temp sensor slope and voltage specs. • Updated "I2C switching specifications". • In "SDHC specifications", removed the operating voltage limits and updated the SD1 and SD6 specs. • In "I2S switching specifications", added separate specification tables for the full operating voltage range.